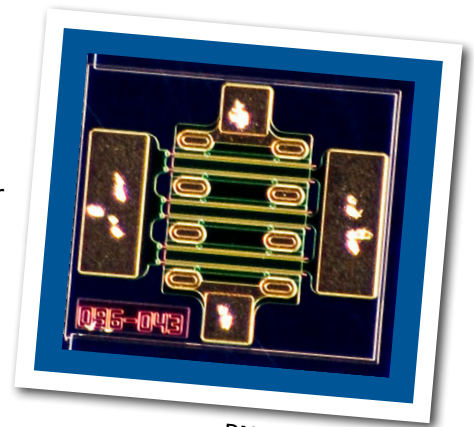


CGH60008D

8 W, 6.0 GHz, GaN HEMT Die

Cree's CGH60008D is a gallium nitride (GaN) High Electron Mobility Transistor (HEMT). GaN has superior properties compared to silicon or gallium arsenide, including higher breakdown voltage, higher saturated electron drift velocity, and higher thermal conductivity. GaN HEMTs offer greater power density and wider bandwidths compared to Si and GaAs transistors.



PN: CGH60008D

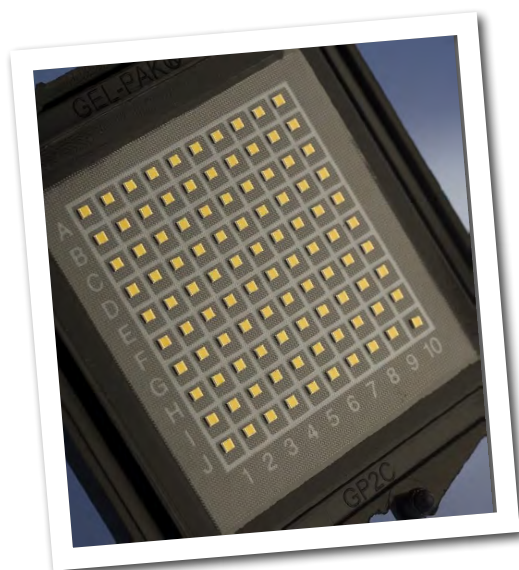
FEATURES

- 15 dB Typical Small Signal Gain at 4 GHz
- 12 dB Typical Small Signal Gain at 6 GHz
- 8 W Typical P_{SAT} @ 28 V Operation
- 5 W Typical P_{SAT} @ 20 V Operation
- High Breakdown Voltage
- High Temperature Operation
- Up to 6 GHz Operation
- High Efficiency

APPLICATIONS

- 2-Way Private Radio
- Broadband Amplifiers
- Cellular Infrastructure
- Test Instrumentation
- Class A, AB, Linear amplifiers suitable for OFDM, W-CDMA, EDGE, CDMA waveforms

Packaging Information



- Bare die are shipped in Gel-Pak® containers.
- Non-adhesive tacky membrane immobilizes die during shipment.

Large Signal Models Available for SiC & GaN



Absolute Maximum Ratings (not simultaneous) at 25 °C

Parameter	Symbol	Rating	Units	Conditions
Drain-source Voltage	V_{DS}	84	VDC	25 °C
Gate-source Voltage	V_{GS}	-10, +2	VDC	25 °C
Storage Temperature	T_{STG}	-65, +150	°C	
Operating Junction Temperature	T_J	225	°C	
Maximum Forward Gate Current	I_{GMAX}	2.1	mA	25 °C
Maximum Drain Current ¹	I_{DMAX}	0.75	A	25 °C
Thermal Resistance, Junction to Case (packaged) ²	$R_{\theta JC}$	8.9	°C/W	
Thermal Resistance, Junction to Case (die only)	$R_{\theta JC}$	5.7	°C/W	85 °C
Mounting Temperature (30 seconds)	T_S	320	°C	30 seconds

Note¹ Current limit for long term, reliable operation

Note² Eutectic die attach using 80/20 AuSn mounted to a 20 mil thick Cu carrier.

Electrical Characteristics (Frequency = 4 GHz unless otherwise stated; $T_C = 25 °C$)

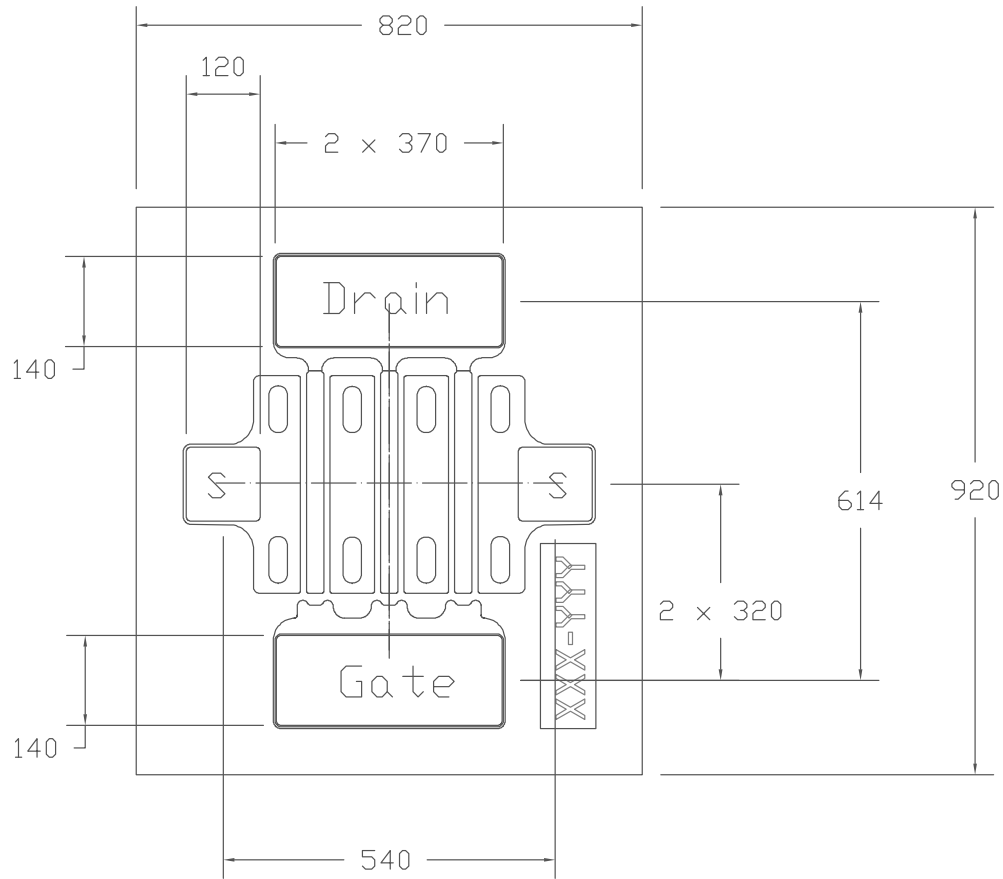
Characteristics	Symbol	Min.	Typ.	Max.	Units	Conditions
DC Characteristics						
Gate Threshold Voltage	$V_{GS(TH)}$	-3.8	-3.0	-2.3	V	$V_{DS} = 10 V, I_D = 2.1 mA$
Gate Quiescent Voltage	$V_{GS(Q)}$	-	-2.7	-	V _{DC}	$V_{DD} = 28 V, I_{DQ} = 60 mA$
Drain Current	I_{DS}	1.75	2.1	-	A	$V_{DS} = 6.0 V, V_{GS} = 2.0 V$
Drain-Source Breakdown Voltage	V_{BD}	120	-	-	V	$V_{GS} = -8 V, I_D = 2.1 mA$
On Resistance	R_{ON}	-	1.6	-	Ω	$V_{DS} = 0.1 V$
Gate Forward Voltage	V_{G-ON}	-	1.9	-	V	$I_{GS} = 2.1 mA$
RF Characteristics						
Small Signal Gain	G_{SS}	-	15	-	dB	$V_{DD} = 28 V, I_{DQ} = 60 mA$
Saturated Power Output ¹	P_{SAT}	-	8	-	W	$V_{DD} = 28 V, I_{DQ} = 60 mA$
Drain Efficiency ²	η	-	65	-	%	$V_{DD} = 28 V, I_{DQ} = 60 mA, P_{SAT}$
Intermodulation Distortion	IM3	-	-30	-	dBc	$V_{DD} = 28 V, I_{DQ} = 60 mA,$ $P_{OUT} = 8 W PEP$
Output Mismatch Stress	VSWR	-	-	10 : 1	Ψ	No damage at all phase angles, $V_{DD} = 28 V, I_{DQ} = 60 mA,$ $P_{OUT} = 8 W CW$
Dynamic Characteristics						
Input Capacitance	C_{GS}	-	2.5	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$
Output Capacitance	C_{DS}	-	0.5	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$
Feedback Capacitance	C_{GD}	-	0.1	-	pF	$V_{DS} = 28 V, V_{GS} = -8 V, f = 1 MHz$

Notes:

¹ P_{SAT} is defined as $I_G = 0.2 mA$.

² Drain Efficiency = P_{OUT} / P_{DC}

DIE Dimensions (units in microns)



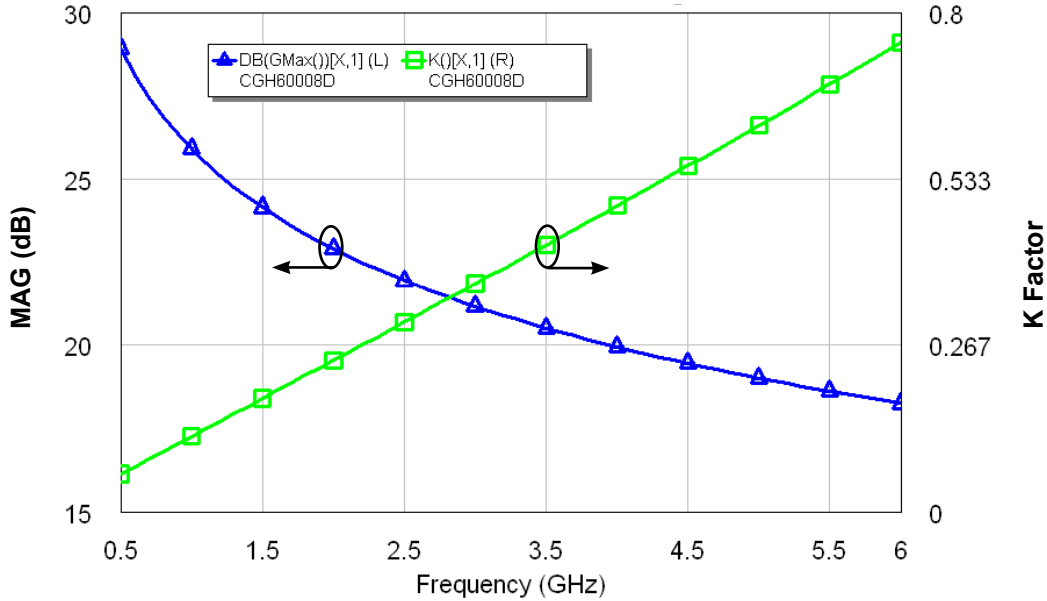
Overall die size 820 x 920 (+0/- 50) microns, die thickness 100 (+/- 10) microns.
All Gate and Drain pads must be wire bonded for electrical connection.

Assembly Notes:

- Recommended solder is AuSn (80/20) solder. Refer to Cree's website for the Eutectic Die Bond Procedure application note at http://www.cree.com/products/wireless_documents.asp
- Vacuum collet is the preferred method of pick-up.
- The backside of the die is the Source (ground) contact.
- Die back side gold plating is 5 microns thick minimum.
- Thermosonic ball or wedge bonding are the preferred connection methods.
- Gold wire must be used for connections.
- Use the die label (XXX-YYY) for correct orientation.

Typical Performance

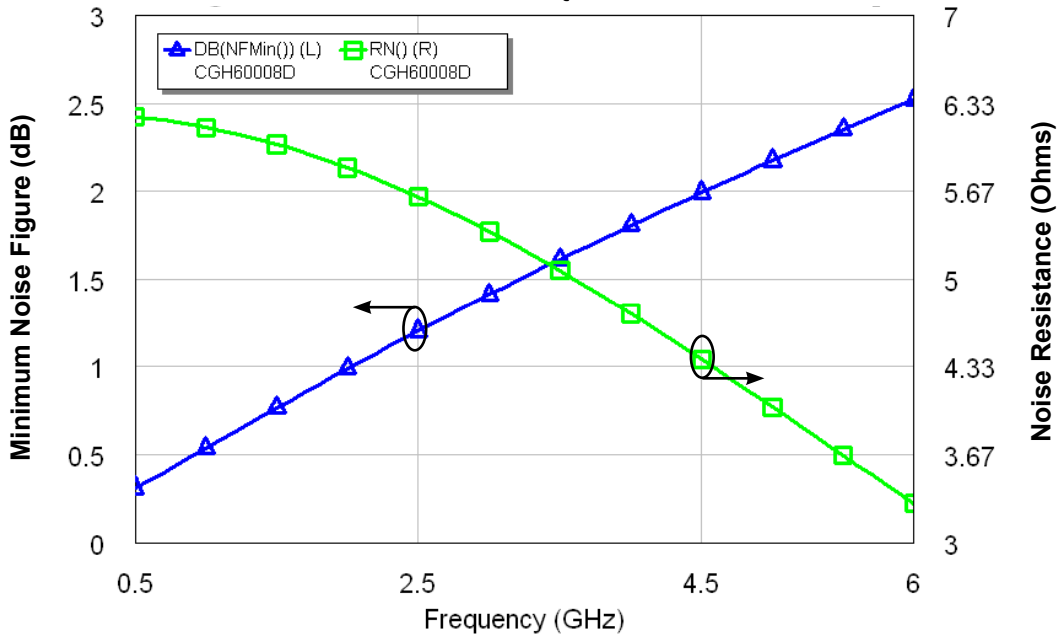
Simulated Maximum Available Gain and K Factor of the CGH60008D
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 100\text{ mA}$



Intrinsic die parameters - reference planes at centers of gate and drain bonding pads. No wire bonds assumed.

Typical Noise Performance

Simulated Minimum Noise Figure and Noise Resistance vs Frequency of the CGH60008D
 $V_{DD} = 28\text{ V}$, $I_{DQ} = 100\text{ mA}$





Typical Die S-Parameters (Small Signal, $V_{DS} = 28\text{ V}$, $I_{DQ} = 60\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.949	-88.97	19.19	130.14	0.025	40.93	0.457	-46.50
600 MHz	0.940	-99.46	17.32	124.14	0.027	35.09	0.426	-51.93
700 MHz	0.933	-108.14	15.69	119.09	0.028	30.19	0.400	-56.47
800 MHz	0.928	-115.36	14.27	114.78	0.029	26.04	0.379	-60.31
900 MHz	0.923	-121.43	13.05	111.05	0.030	22.47	0.363	-63.61
1.0 GHz	0.920	-126.58	12.00	107.79	0.031	19.36	0.350	-66.51
1.1 GHz	0.917	-130.99	11.08	104.89	0.031	16.62	0.340	-69.08
1.2 GHz	0.914	-134.80	10.28	102.28	0.032	14.18	0.332	-71.39
1.3 GHz	0.913	-138.12	9.58	99.92	0.032	11.97	0.327	-73.50
1.4 GHz	0.911	-141.05	8.96	97.76	0.032	9.97	0.323	-75.45
1.5 GHz	0.910	-143.64	8.41	95.76	0.032	8.12	0.320	-77.26
1.6 GHz	0.909	-145.94	7.92	93.89	0.032	6.42	0.319	-78.96
1.7 GHz	0.908	-148.02	7.48	92.15	0.032	4.83	0.319	-80.57
1.8 GHz	0.908	-149.89	7.08	90.50	0.033	3.34	0.319	-82.10
1.9 GHz	0.907	-151.59	6.72	88.93	0.033	1.93	0.321	-83.55
2.0 GHz	0.907	-153.14	6.39	87.44	0.033	0.60	0.323	-84.95
2.1 GHz	0.907	-154.56	6.09	86.02	0.033	-0.67	0.325	-86.29
2.2 GHz	0.906	-155.86	5.82	84.65	0.033	-1.88	0.329	-87.59
2.3 GHz	0.906	-157.07	5.56	83.33	0.033	-3.04	0.332	-88.84
2.4 GHz	0.906	-158.19	5.33	82.06	0.033	-4.16	0.336	-90.06
2.5 GHz	0.906	-159.24	5.11	80.82	0.033	-5.23	0.340	-91.24
2.6 GHz	0.906	-160.21	4.91	79.62	0.033	-6.28	0.344	-92.39
2.7 GHz	0.906	-161.12	4.72	78.45	0.032	-7.29	0.349	-93.51
2.8 GHz	0.906	-161.98	4.55	77.31	0.032	-8.27	0.354	-94.60
2.9 GHz	0.906	-162.79	4.38	76.20	0.032	-9.22	0.359	-95.66
3.0 GHz	0.906	-163.55	4.23	75.11	0.032	-10.15	0.364	-96.70
3.2 GHz	0.906	-164.95	3.95	73.01	0.032	-11.94	0.375	-98.72
3.4 GHz	0.907	-166.23	3.70	70.97	0.032	-13.66	0.386	-100.66
3.6 GHz	0.907	-167.38	3.48	69.01	0.032	-15.31	0.397	-102.54
3.8 GHz	0.908	-168.44	3.28	67.10	0.032	-16.90	0.408	-104.34
4.0 GHz	0.908	-169.43	3.10	65.24	0.031	-18.44	0.420	-106.09
4.2 GHz	0.909	-170.34	2.93	63.43	0.031	-19.93	0.432	-107.79
4.4 GHz	0.909	-171.19	2.78	61.67	0.031	-21.38	0.443	-109.44
4.6 GHz	0.910	-171.99	2.64	59.94	0.031	-22.79	0.455	-111.05
4.8 GHz	0.910	-172.74	2.51	58.25	0.030	-24.17	0.467	-112.61
5.0 GHz	0.911	-173.46	2.39	56.59	0.030	-25.51	0.478	-114.14
5.2 GHz	0.912	-174.14	2.28	54.97	0.030	-26.82	0.489	-115.63
5.4 GHz	0.912	-174.79	2.18	53.37	0.030	-28.09	0.500	-117.08
5.6 GHz	0.913	-175.41	2.09	51.81	0.029	-29.34	0.511	-118.50
5.8 GHz	0.914	-176.01	2.00	50.27	0.029	-30.57	0.522	-119.89
6.0 GHz	0.914	-176.58	1.92	48.75	0.029	-31.76	0.533	-121.25

Contact Cree to receive this s-parameter file in ".s2p" format at Wireless_Sales@cree.com



Typical Die S-Parameters (Small Signal, $V_{DS} = 28\text{ V}$, $I_{DQ} = 120\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.938	-100.12	21.07	124.88	0.030	35.53	0.466	-62.41
600 MHz	0.929	-110.15	18.68	119.23	0.032	30.01	0.428	-69.18
700 MHz	0.923	-118.17	16.69	114.61	0.034	25.53	0.399	-74.78
800 MHz	0.918	-124.66	15.03	110.76	0.035	21.80	0.376	-79.46
900 MHz	0.914	-129.99	13.63	107.48	0.035	18.66	0.358	-83.42
1.0 GHz	0.911	-134.43	12.45	104.64	0.036	15.95	0.344	-86.81
1.1 GHz	0.909	-138.17	11.44	102.15	0.036	13.59	0.334	-89.73
1.2 GHz	0.908	-141.36	10.58	99.92	0.037	11.50	0.326	-92.27
1.3 GHz	0.906	-144.11	9.82	97.91	0.037	9.62	0.320	-94.48
1.4 GHz	0.905	-146.49	9.16	96.08	0.037	7.91	0.316	-96.43
1.5 GHz	0.905	-148.59	8.58	94.39	0.037	6.35	0.314	-98.16
1.6 GHz	0.904	-150.43	8.07	92.82	0.037	4.91	0.313	-99.70
1.7 GHz	0.904	-152.08	7.61	91.34	0.037	3.57	0.312	-101.09
1.8 GHz	0.903	-153.55	7.19	89.96	0.037	2.32	0.313	-102.34
1.9 GHz	0.903	-154.87	6.82	88.64	0.037	1.14	0.314	-103.47
2.0 GHz	0.903	-156.06	6.48	87.39	0.037	0.02	0.316	-104.51
2.1 GHz	0.903	-157.14	6.17	86.20	0.037	-1.05	0.319	-105.46
2.2 GHz	0.903	-158.13	5.89	85.05	0.037	-2.07	0.321	-106.35
2.3 GHz	0.903	-159.04	5.63	83.94	0.037	-3.04	0.325	-107.17
2.4 GHz	0.903	-159.87	5.39	82.87	0.037	-3.98	0.328	-107.95
2.5 GHz	0.903	-160.64	5.17	81.83	0.037	-4.89	0.332	-108.67
2.6 GHz	0.903	-161.35	4.97	80.82	0.037	-5.76	0.336	-109.36
2.7 GHz	0.903	-162.00	4.78	79.84	0.037	-6.61	0.341	-110.02
2.8 GHz	0.903	-162.62	4.60	78.89	0.037	-7.44	0.345	-110.64
2.9 GHz	0.903	-163.19	4.43	77.95	0.037	-8.24	0.350	-111.25
3.0 GHz	0.903	-163.72	4.28	77.04	0.037	-9.02	0.355	-111.83
3.2 GHz	0.904	-164.69	3.99	75.27	0.037	-10.53	0.365	-112.93
3.4 GHz	0.904	-165.55	3.74	73.56	0.037	-11.98	0.376	-113.98
3.6 GHz	0.905	-166.31	3.52	71.91	0.036	-13.37	0.387	-114.98
3.8 GHz	0.906	-167.00	3.32	70.31	0.036	-14.71	0.398	-115.94
4.0 GHz	0.906	-167.62	3.13	68.75	0.036	-16.00	0.409	-116.88
4.2 GHz	0.907	-168.18	2.97	67.23	0.036	-17.26	0.420	-117.79
4.4 GHz	0.908	-168.70	2.81	65.75	0.036	-18.48	0.431	-118.68
4.6 GHz	0.909	-169.17	2.67	64.30	0.035	-19.67	0.442	-119.55
4.8 GHz	0.909	-169.61	2.55	62.89	0.035	-20.82	0.453	-120.40
5.0 GHz	0.910	-170.02	2.43	61.50	0.035	-21.95	0.464	-121.25
5.2 GHz	0.911	-170.40	2.32	60.14	0.035	-23.05	0.475	-122.08
5.4 GHz	0.912	-170.75	2.22	58.80	0.034	-24.12	0.486	-122.89
5.6 GHz	0.913	-171.08	2.12	57.49	0.034	-25.17	0.497	-123.70
5.8 GHz	0.914	-171.39	2.03	56.20	0.034	-26.20	0.507	-124.50
6.0 GHz	0.914	-171.69	1.95	54.94	0.033	-27.20	0.517	-125.28

Contact Cree to receive this s-parameter file in ".s2p" format at Wireless_Sales@cree.com



Typical Die S-Parameters (Small Signal, $V_{DS} = 28\text{ V}$, $I_{DQ} = 300\text{ mA}$, magnitude / angle)

Frequency	Mag S11	Ang S11	Mag S21	Ang S21	Mag S12	Ang S12	Mag S22	Ang S22
500 MHz	0.937	-108.13	22.00	121.21	0.028	31.85	0.404	-72.20
600 MHz	0.930	-117.71	19.30	115.84	0.029	26.61	0.372	-79.50
700 MHz	0.925	-125.21	17.11	111.51	0.030	22.42	0.348	-85.45
800 MHz	0.921	-131.20	15.31	107.94	0.031	18.98	0.330	-90.35
900 MHz	0.918	-136.06	13.83	104.92	0.031	16.09	0.317	-94.43
1.0 GHz	0.916	-140.08	12.59	102.31	0.032	13.61	0.307	-97.85
1.1 GHz	0.915	-143.44	11.54	100.03	0.032	11.46	0.300	-100.74
1.2 GHz	0.913	-146.29	10.65	97.99	0.032	9.55	0.295	-103.19
1.3 GHz	0.913	-148.74	9.88	96.15	0.032	7.85	0.292	-105.28
1.4 GHz	0.912	-150.86	9.20	94.47	0.033	6.30	0.290	-107.07
1.5 GHz	0.911	-152.71	8.61	92.92	0.033	4.88	0.289	-108.62
1.6 GHz	0.911	-154.34	8.09	91.48	0.033	3.56	0.289	-109.96
1.7 GHz	0.911	-155.79	7.62	90.12	0.033	2.34	0.290	-111.13
1.8 GHz	0.910	-157.09	7.20	88.84	0.033	1.19	0.292	-112.16
1.9 GHz	0.910	-158.25	6.83	87.63	0.033	0.11	0.294	-113.08
2.0 GHz	0.910	-159.30	6.49	86.47	0.033	-0.92	0.297	-113.89
2.1 GHz	0.910	-160.25	6.17	85.36	0.033	-1.90	0.300	-114.62
2.2 GHz	0.910	-161.12	5.89	84.29	0.033	-2.84	0.303	-115.28
2.3 GHz	0.910	-161.92	5.63	83.26	0.033	-3.74	0.307	-115.88
2.4 GHz	0.910	-162.65	5.39	82.26	0.033	-4.61	0.311	-116.43
2.5 GHz	0.910	-163.32	5.17	81.29	0.033	-5.44	0.315	-116.94
2.6 GHz	0.910	-163.95	4.97	80.35	0.033	-6.26	0.320	-117.42
2.7 GHz	0.910	-164.52	4.77	79.43	0.033	-7.05	0.324	-117.87
2.8 GHz	0.911	-165.06	4.60	78.54	0.032	-7.81	0.329	-118.30
2.9 GHz	0.911	-165.56	4.43	77.66	0.032	-8.56	0.334	-118.70
3.0 GHz	0.911	-166.03	4.28	76.80	0.032	-9.29	0.339	-119.09
3.2 GHz	0.911	-166.88	3.99	75.13	0.032	-10.70	0.349	-119.83
3.4 GHz	0.912	-167.63	3.74	73.51	0.032	-12.05	0.360	-120.53
3.6 GHz	0.912	-168.31	3.52	71.94	0.032	-13.36	0.371	-121.21
3.8 GHz	0.913	-168.91	3.32	70.42	0.032	-14.62	0.382	-121.87
4.0 GHz	0.913	-169.46	3.13	68.94	0.032	-15.85	0.393	-122.52
4.2 GHz	0.914	-169.95	2.97	67.49	0.031	-17.03	0.404	-123.16
4.4 GHz	0.914	-170.41	2.82	66.07	0.031	-18.19	0.415	-123.79
4.6 GHz	0.915	-170.83	2.68	64.68	0.031	-19.32	0.426	-124.43
4.8 GHz	0.916	-171.21	2.55	63.32	0.031	-20.42	0.437	-125.06
5.0 GHz	0.916	-171.57	2.43	61.99	0.031	-21.49	0.448	-125.69
5.2 GHz	0.917	-171.91	2.33	60.68	0.030	-22.54	0.458	-126.32
5.4 GHz	0.918	-172.22	2.22	59.39	0.030	-23.57	0.469	-126.95
5.6 GHz	0.919	-172.51	2.13	58.12	0.030	-24.58	0.480	-127.57
5.8 GHz	0.919	-172.79	2.04	56.88	0.030	-25.56	0.490	-128.20
6.0 GHz	0.920	-173.05	1.96	55.66	0.029	-26.53	0.500	-128.82

Contact Cree to receive this s-parameter file in ".s2p" format at Wireless_Sales@cree.com



Disclaimer

Specifications are subject to change without notice. Cree, Inc. believes the information contained within this data sheet to be accurate and reliable. However, no responsibility is assumed by Cree for its use or for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of Cree. Cree makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose. "Typical" parameters are the average values expected by Cree in large quantities and are provided for information purposes only. These values can and do vary in different applications, and actual performance can vary over time. All operating parameters should be validated by customer's technical experts for each application. Cree products are not designed, intended, or authorized for use as components in applications intended for surgical implant into the body or to support or sustain life, in applications in which the failure of the Cree product could result in personal injury or death, or in applications for the planning, construction, maintenance or direct operation of a nuclear facility. CREE and the CREE logo are registered trademarks of Cree, Inc.

For more information, please contact:

Cree, Inc.
4600 Silicon Drive
Durham, North Carolina, USA 27703
www.cree.com/wireless

Sarah Miller
Marketing & Export
Cree, RF Components
1.919.407.5302

Ryan Baker
Marketing
Cree, RF Components
1.919.407.7816

Tom Dekker
Sales Director
Cree, RF Components
1.919.407.5639



Компания «ЭлектроПласт» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов;
- Поставка более 17-ти миллионов наименований электронных компонентов;
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- Лицензия ФСБ на осуществление работ с использованием сведений, составляющих государственную тайну;
- Поставка специализированных компонентов (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Aeroflex, Peregrine, Syfer, Eurofarad, Texas Instrument, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Помимо этого, одним из направлений компании «ЭлектроПласт» является направление «Источники питания». Мы предлагаем Вам помощь Конструкторского отдела:

- Подбор оптимального решения, техническое обоснование при выборе компонента;
- Подбор аналогов;
- Консультации по применению компонента;
- Поставка образцов и прототипов;
- Техническая поддержка проекта;
- Защита от снятия компонента с производства.



Как с нами связаться

Телефон: 8 (812) 309 58 32 (многоканальный)

Факс: 8 (812) 320-02-42

Электронная почта: org@eplast1.ru

Адрес: 198099, г. Санкт-Петербург, ул. Калинина, дом 2, корпус 4, литера А.